



#### N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
601/	5Ω @ V <sub>GS</sub> = 10V	230mA
60V	7.5Ω @ V <sub>GS</sub> = 5V	190mA

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- Power Management Functions

## **Features and Benefits**

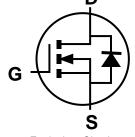
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. <a href="https://www.diodes.com/quality/product-definitions/">https://www.diodes.com/quality/product-definitions/</a>

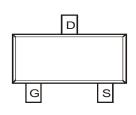
### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (23)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

SOT23 (Standard)







Top View

**Equivalent Circuit** 

Top View

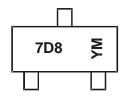
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMN67D8L-7	SOT23 (Standard)	3,000/Tape & Reel
DMN67D8L-13	SOT23 (Standard)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



7D8 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: I = 2021) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Date Code Rey												
Year	2015		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	С		- 1	J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

DMN67D8L
Document number: DS38024 Rev. 2 - 2

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## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	60	V		
Gate-Source Voltage			Vgss	±30	V
Continuous Drain Current (Note 6) Vgs = 10V	lσ	230 170	mA		
Maximum Body Diode Forward Current (Note 6)		Is	230	mA	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 19	%)		I <sub>DM</sub>	800	mA

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	340	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>0JA</sub>	376	°C/W
Total Power Dissipation (Note 6)		PD	570	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	224	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

# Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60		_	V	$V_{GS} = 0V, I_{D} = 10\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	1.0	μΑ	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	Igss			±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0		2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Process		1.4	7.5	Ω	$V_{GS} = 5V, I_{D} = 0.05A$	
Static Drain-Source Off-Nesistance	R <sub>DS(ON)</sub>		1.3	5.0	5.2	$V_{GS} = 10V, I_D = 0.5A$	
Forward Transconductance	<b>g</b> FS	80		_	mS	$V_{DS} = 10V, I_{D} = 0.2A$	
Diode Forward Voltage	VsD	_	0.78	1.5	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	22	_	pF	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Output Capacitance	Coss	_	4.1	_	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, -f = 1.0MHz	
Reverse Transfer Capacitance	Crss		2.5	_	pF	1 = 1.01/1112	
Gate Resistance	Rg	_	120	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	361	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	821	_	200	\/ 40\/ I- 050m A	
Gate-Source Charge	$Q_{gs}$	_	162	_	рC	$V_{DS} = 10V, I_{D} = 250mA$	
Gate-Drain Charge	$Q_{gd}$	_	116	_			
Turn-On Delay Time	td(ON)	_	2.8	_		V 00V I 0.0A	
Turn-On Rise Time	t <sub>R</sub>	_	3.0	_	ne	$V_{DD} = 30V$ , $I_D = 0.2A$ ,	
Turn-Off Delay Time	tD(OFF)	_	7.6	_	ns	$R_L = 150\Omega$ , $V_{GEN} = 10V$ , $R_{GEN} = 25\Omega$	
Turn-Off Fall Time	tF	_	5.6	_		11GEN - 2012	

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. copper, single sided.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.



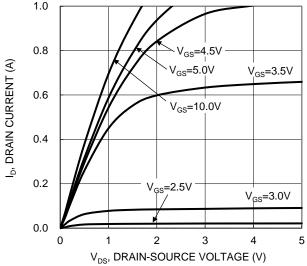


Figure 1. Typical Output Characteristic

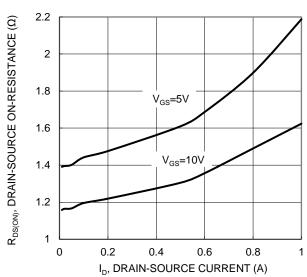


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

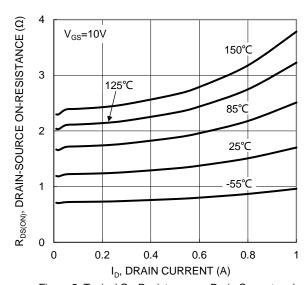
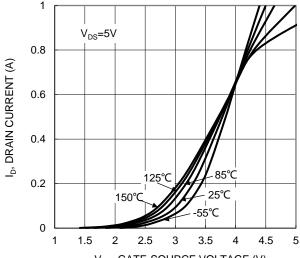
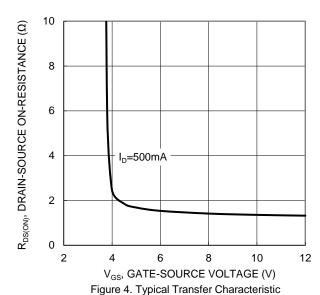


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic



2 R<sub>DS(ON)</sub>, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 1.8  $V_{GS}=10V$ ,  $I_D=500mA$ 1.6 1.4 1.2  $V_{GS}=5V$ ,  $I_D=50mA$ 1 0.8 0.6 -50 -25 0 25 50 75 100 125 150 T<sub>.i</sub>, JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Junction Temperature



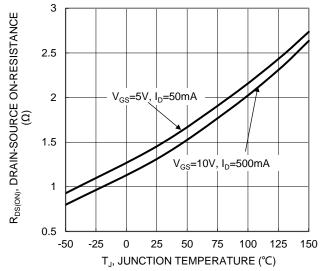
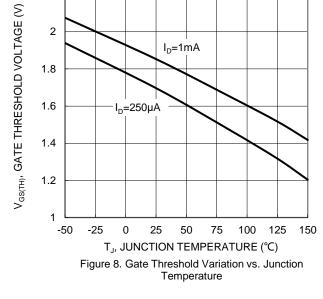


Figure 7. On-Resistance Variation with Junction Temperature



2.2

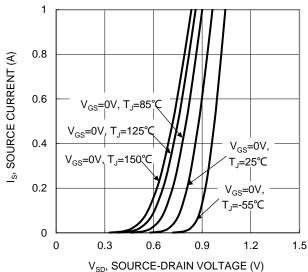
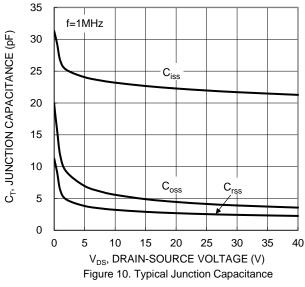
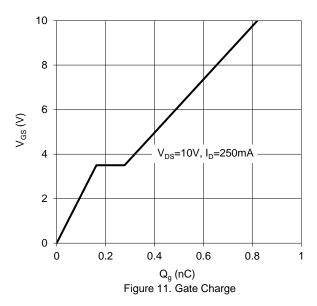
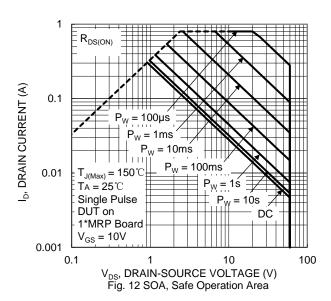


Figure 9. Diode Forward Voltage vs. Current









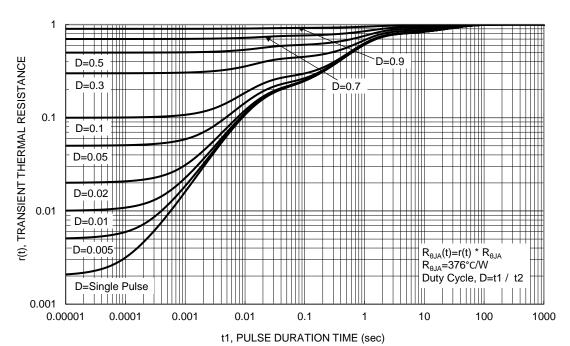


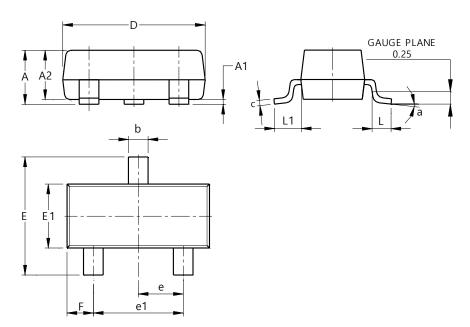
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23 (Standard)

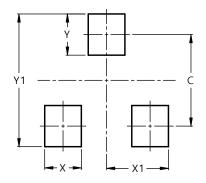


SOT23 (Standard)							
Dim	Min	Max	Тур				
Α	0.90	1.15	1.025				
A1	0.00	0.10	0.05				
A2	0.85	1.10	0.975				
b	0.30	0.51	0.40				
С	0.080	0.202	0.11				
D	2.80	3.00	2.90				
Е	2.25	2.55	2.40				
E1	1.20	1.40	1.30				
е	0.89	1.03	0.915				
e1	1.78	2.05	1.83				
F	0.40	0.60	0.535				
L1	0.45	0.61	0.55				
L	0.25	0.55	0.40				
а	0°	8°					
All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23 (Standard)



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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